## 1. General description

NPN/PNP Resistor-Equipped double Transistors (RET) in a leadless ultra small DFN1412-6 (SOT1268) Surface-Mounted Device (SMD) plastic package.

#### 2. Features and benefits

- · 100 mA output current capability
- · Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- · Reduces pick and place costs
- Low package height of 0.5 mm
- AEC-Q101 qualified

## 3. Applications

- Digital applications
- Cost-saving alternative to BC847/BC857 series in digital applications
- Control of IC inputs
- Switching loads

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Per transistor,	Per transistor, for the PNP transistor with negative polarity							
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-	50	V	
Io	output current			-	-	100	mA	
h <sub>FE</sub>	DC current gain	$V_{CE}$ = 5 V; $I_{C}$ = 5 mA; $T_{amb}$ = 25 °C		60	-	-		
R1	bias resistor 1		[1]	15.4	22	28.6	kΩ	
R2/R1	bias resistor ratio		[1]	0.8	1	1.2		

[1] See section "Test information" for resistor calculation and test conditions.



50 V, 100 mA NPN/PNP Resistor-Equipped double Transistors (RET)

# 5. Pinning information

### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND1	GND (emitter) TR1		O1 I2 GND2
2	I1	input ( base) TR1	7 6	
3	O2	output (collector) TR2	2 5	R1 R2
4	GND2	GND (emitter) TR2		TR1 TR2
5	12	input ( base) TR2	3 6 4	R2 R1
6	01	output (collector) TR1	Transparent top view	
7	O1	output (collector) TR1	DFN1412-6 (SOT1268)	GND1 I1 O2
8	O2	output (collector) TR2	, ,	aaa-007379

# 6. Ordering information

### **Table 3. Ordering information**

Type number	Package	kage				
	Name	Description	Version			
PRMD2	DFN1412-6	plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals; body: 1.4 mm x 1.2 mm x 0.47 mm	SOT1268			

# 7. Marking

### **Table 4. Marking codes**

Type number	Marking code
PRMD2	B4

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50 V, 100 mA NPN/PNP Resistor-Equipped double Transistors (RET)

# 8. Limiting values

#### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transist	or, for the PNP transistor wit	h negative polarity				
$V_{CBO}$	collector-base voltage	open emitter		-	50	V
$V_{CEO}$	collector-emitter voltage	open base		-	50	V
$V_{EBO}$	emitter-base voltage	open collector		-	10	V
VI	input voltage			-10	40	V
Io	output current			-	100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	325	mW
Per device						
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	480	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

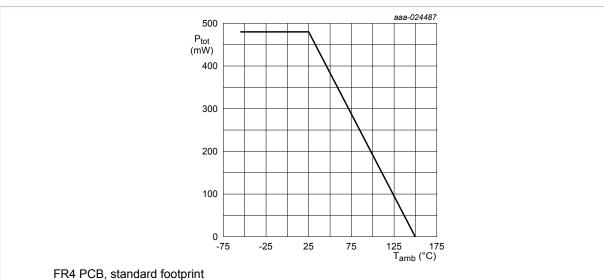


Fig. 1. Per device: Power derating curve

50 V, 100 mA NPN/PNP Resistor-Equipped double Transistors (RET)

### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transis	tor					,	
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	385	K/W
Per device	,						,
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	-	261	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

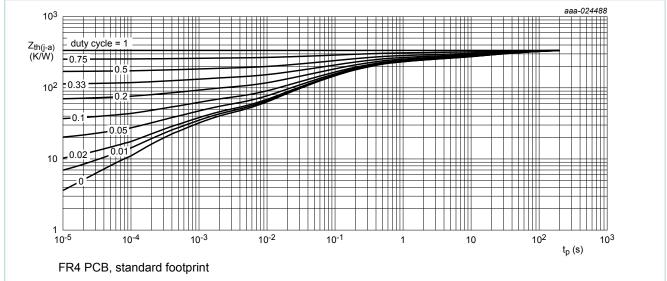


Fig. 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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50 V, 100 mA NPN/PNP Resistor-Equipped double Transistors (RET)

## 10. Characteristics

#### **Table 7. Characteristics**

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	or, for the PNP transistor v	with negative polarity					
I <sub>CBO</sub>	collector-base cut-off current (emitter open)	$V_{CB} = 50 \text{ V}; I_{E} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		-	-	100	nA
CLO	collector-emitter cut-off	$V_{CE}$ = 30 V; $I_{B}$ = 0 A; $T_{amb}$ = 25 °C		-	-	1	μΑ
	current (base open)	$V_{CE}$ = 30 V; $I_{B}$ = 0 A; $T_{j}$ = 150 °C		-	-	5	μA
I <sub>EBO</sub>	emitter-base cut-off current (collector open)	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		-	-	180	μA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = 5 V; $I_{C}$ = 5 mA; $T_{amb}$ = 25 °C		60	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}; T_{amb} = 25 \text{ °C}$		-	-	150	mV
$V_{I(off)}$	off-state input voltage	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 100 μA; T <sub>amb</sub> = 25 °C		-	1.1	8.0	V
$V_{I(on)}$	on-state input voltage	$V_{CE}$ = 0.3 V; $I_{C}$ = 5 mA; $T_{amb}$ = 25 °C		2.5	1.7	-	V
R1	bias resistor 1		[1]	15.4	22	28.6	kΩ
R2/R1	bias resistor ratio		[1]	0.8	1	1.2	
C <sub>C</sub>	collector capacitance	$V_{CB}$ = 10 V; $I_{E}$ = 0 A; $i_{e}$ = 0 A; $f$ = 1 MHz; $T_{amb}$ = 25 °C		-	-	2.5	pF
		$V_{CB}$ = -10 V; $I_{E}$ = 0 mA; $i_{e}$ = 0 mA; $f$ = 1 MHz; $T_{amb}$ = 25 °C		-	-	3	pF
f <sub>T</sub>	transition frequency	$V_{CE}$ = 5 V; $I_{C}$ = 10 mA; f = 100 MHz; $T_{amb}$ = 25 °C	[2]	-	230	-	MHz
		$V_{CE}$ = -5 V; $I_{C}$ = -10 mA; f = 100 MHz; $T_{amb}$ = 25 °C		-	180	-	MHz

<sup>[1]</sup> See section "Test information" for resistor calculation and test conditions.

<sup>[2]</sup> Characteristics of built-in transistor

#### 50 V, 100 mA NPN/PNP Resistor-Equipped double Transistors (RET)

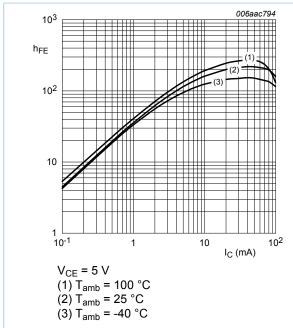


Fig. 3. NPN transistor: DC current gain as a function of collector current; typical values

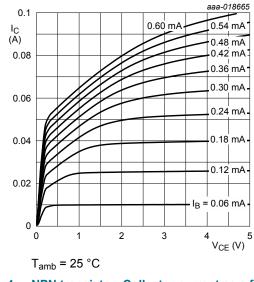
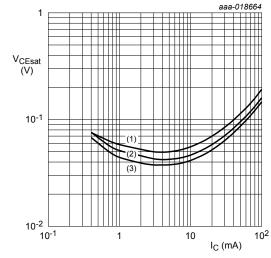
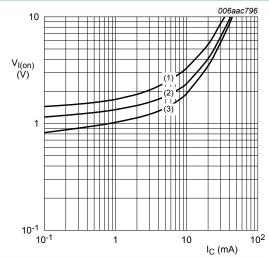


Fig. 4. NPN transistor: Collector current as a function of collector-emitter voltage; typical values



 $I_C/I_B = 20$ (1)  $T_{amb} = 100 \,^{\circ}C$ (2)  $T_{amb} = 25 \,^{\circ}C$ (3)  $T_{amb} = -40 \,^{\circ}C$ 

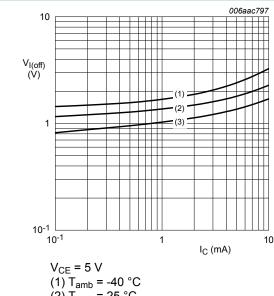
Fig. 5. NPN transistor: Collector-emitter saturation voltage as a function of collector current; typical values



V<sub>CE</sub> = 0.3 V (1) T<sub>amb</sub> = -40 °C (2) T<sub>amb</sub> = 25 °C (3) T<sub>amb</sub> = 100 °C

Fig. 6. NPN transistor: On-state input voltage as a function of collector current; typical values

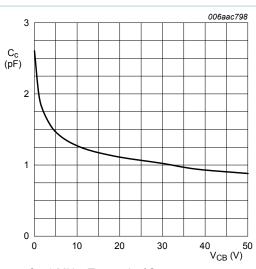
#### 50 V, 100 mA NPN/PNP Resistor-Equipped double Transistors (RET)



(2)  $T_{amb} = 25 \, ^{\circ}C$ 

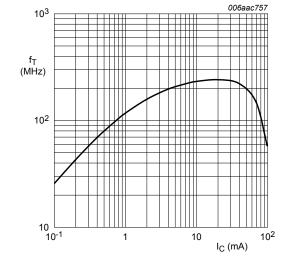
(3)  $T_{amb} = 100 \, ^{\circ}C$ 

NPN transistor: Off-state input voltage as a Fig. 7. function of collector current; typical values



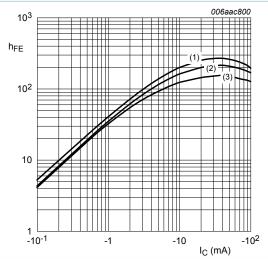
 $f = 1 MHz; T_{amb} = 25 °C$ 

NPN transistor: Collector capacitance as a Fig. 8. function of collector-base voltage; typical values



 $V_{CE}$  = 5 V;  $T_{amb}$  = 25 °C

**NPN** transistor: Transition frequency as a Fig. 9. function of collector current; typical values of built-in transistor



V<sub>CE</sub> = -5 V (1) T<sub>amb</sub> = 100 °C (2) T<sub>amb</sub> = 25 °C (3) T<sub>amb</sub> = -40 °C

Fig. 10. PNP transistor: DC current gain as a function of collector current; typical values

#### 50 V, 100 mA NPN/PNP Resistor-Equipped double Transistors (RET)

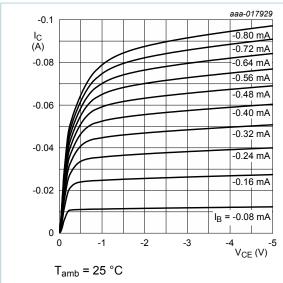
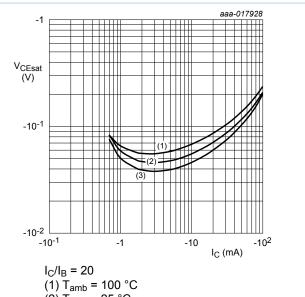
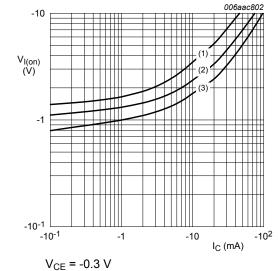


Fig. 11. PNP transistor: Collector current as a function of collector-emitter voltage; typical values



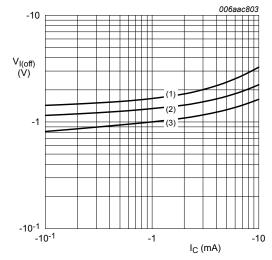
(2)  $T_{amb} = 25 \, ^{\circ}C$ (3)  $T_{amb} = -40 \, ^{\circ}C$ 

Fig. 12. PNP transistor: Collector-emitter saturation voltage as a function of collector current; typical values



(1) T<sub>amb</sub> = -40 °C (2) T<sub>amb</sub> = 25 °C (3) T<sub>amb</sub> = 100 °C

Fig. 13. PNP transistor: On-state input voltage as a function of collector current; typical values



 $V_{CE}$  = -5 V

(1) T<sub>amb</sub> = -40 °C (2) T<sub>amb</sub> = 25 °C (3) T<sub>amb</sub> = 100 °C

Fig. 14. PNP transistor: Off-state input voltage as a function of collector current; typical values

#### 50 V, 100 mA NPN/PNP Resistor-Equipped double Transistors (RET)

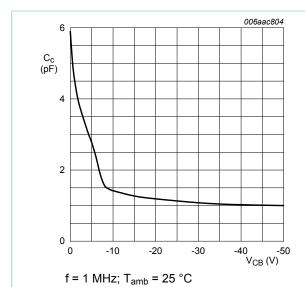


Fig. 15. PNP transistor: Collector capacitance as a function of collector-base voltage; typical values

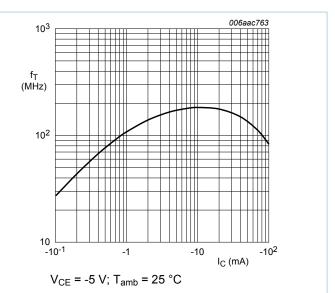


Fig. 16. PNP transistor: Transition frequency as a function of collector current; typical values of built-in transistor

## 11. Test information

### **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

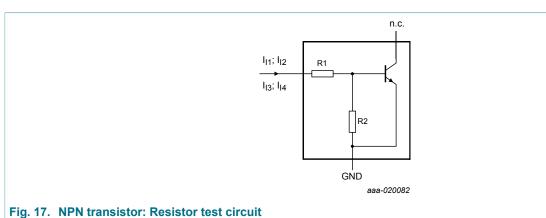
#### **Resistor calculation**

· Calculation of bias resistor 1 (R1)

$$RI = \frac{V(I_{12}) - V(I_{11})}{I_{12} - I_{11}}$$

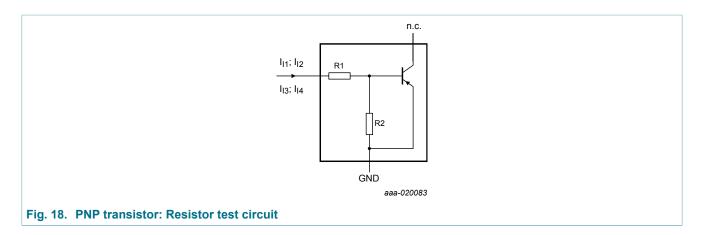
Calculation of bias resistor ratio (R2/R1)

$$\frac{R2}{R1} = \frac{V(I14) - V(I13)}{R1 \cdot (I14 - I13)} - 1$$



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### 50 V, 100 mA NPN/PNP Resistor-Equipped double Transistors (RET)



#### **Resistor test conditions**

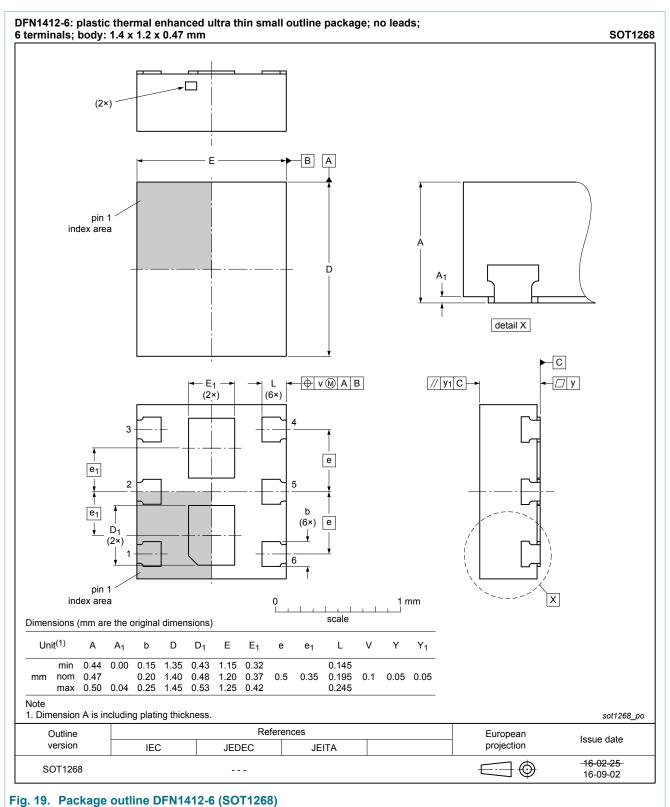
#### **Table 8. Resistor test conditions**

Per transistor; for the PNP transistor with negative polarity

R1 (kΩ)	R2 (kΩ)	Test conditions			
		I <sub>I1</sub>	I <sub>I2</sub>	I <sub>13</sub>	I <sub>14</sub>
22	22	150 µA	230 μΑ	-150 μA	-230 μΑ

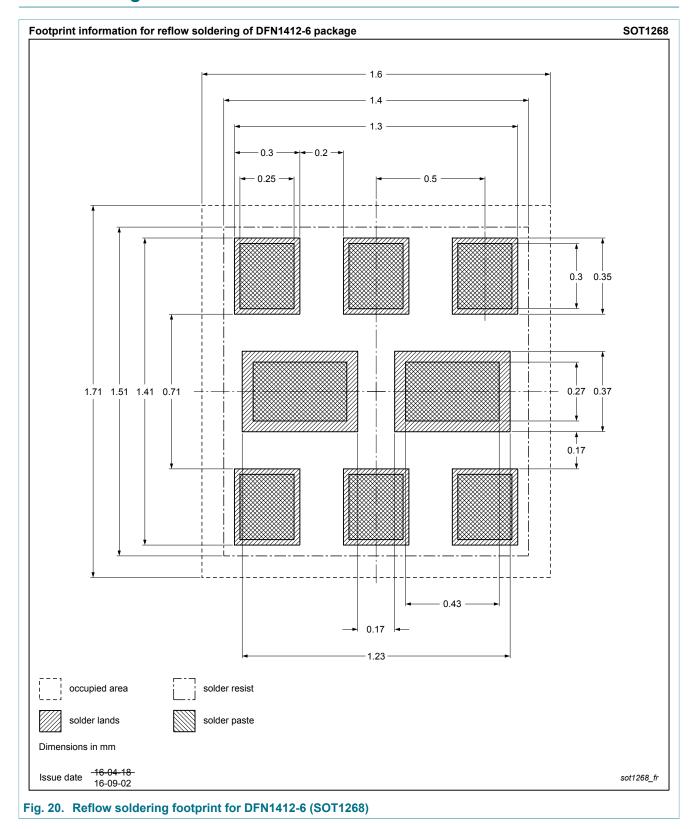
50 V, 100 mA NPN/PNP Resistor-Equipped double Transistors (RET)

## 12. Package outline



50 V, 100 mA NPN/PNP Resistor-Equipped double Transistors (RET)

## 13. Soldering



## 50 V, 100 mA NPN/PNP Resistor-Equipped double Transistors (RET)

# 14. Revision history

### Table 9. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PRMD2 v.1	20170614	Product data sheet	-	-

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#### 50 V, 100 mA NPN/PNP Resistor-Equipped double Transistors (RET)

## 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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PRMD2

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### 50 V, 100 mA NPN/PNP Resistor-Equipped double Transistors (RET)

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